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FDA70N20 N-Channel UniFET™ MOSFET

200 V, 70 A, 35 m Ω

Features

- + $R_{DS(on)}$ = 35 m Ω (Max.) @ V_{GS} = 10 V, I_D = 35 A
- Low Gate Charge (Typ. 66 nC)
- Low Crss (Typ. 89 pF)
- 100% Avalanche Tested

Applications

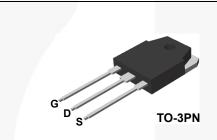
- Uninterruptible Power Supply
- AC-DC Power Supply

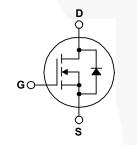


FDA70N20 — N-Channel UniFETTM MOSFET

Description

UniFET[™] MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			Unit		
V _{DSS}	Drain-Source Voltage			200		
ID	Drain Current - Continuous ($T_C = 25$ - Continuous ($T_C = 10$			70 45	A A	
I _{DM}	Drain Current - F	ulsed	(Note 1)	280	A	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2) 1742		mJ	
I _{AR}	Avalanche Current		(Note 1)	70	A	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	41.7	mJ	
dv/dt	Peak Diode Recovery dv/	dt	(Note 3)	4.5	V/ns	
P _D		_C = 25°C) erate Above 25°C		417 3.3	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FDA70N20	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.3	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

FDA70N20
- N-Channel
NOSFET

Part Number FDA70N20		er Top Mark		ackage Packing Method Reel Size		e Ta	ape Width	n Qu	Quantity	
		FDA70N20	TO-3PN			N/A		30 units		
Electric	al Chara	acteristics T _c = 25°C	unless otherwise	noted.						
Symbol		Parameter		Conditions		Min.	Тур.	Max.	Unit	
Off Charac	teristics									
BV _{DSS}	Drain-Sour	ce Breakdown Voltage	$V_{GS} = 0$	V _{GS} = 0V, I _D = 250μA					V	
ΔΒV _{DSS} / ΔT _J	Breakdowr Coefficient	N Voltage Temperature	I _D = 250	$I_D = 250 \mu A$, Referenced to 25°C			0.2		V/∘C	
I _{DSS}	Zero Gate	Voltage Drain Current		$V_{DS} = 200V, V_{GS} = 0V$ $V_{DS} = 160V, T_{C} = 125^{\circ}C$				1 10	μΑ μΑ	
I _{GSSF}	Gate-Body	Leakage Current, Forwar	d V _{GS} = 3	$V_{GS} = 30V, V_{DS} = 0V$				100	nA	
I _{GSSR}	Gate-Body	Leakage Current, Revers	e V _{GS} = -	V _{GS} = -30V, V _{DS} = 0V				-100	nA	
On Charac	teristics									
V _{GS(th)}	Gate Three	shold Voltage	$V_{DS} = V$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		3.0		5.0	V	
R _{DS(on)}	Static Drain On-Resista		V _{GS} = 1	V _{GS} = 10V, I _D = 35A			0.029	0.035	Ω	
9 _{FS}	Forward Tr	ransconductance	V _{DS} = 4	V _{DS} = 40V, I _D = 35A			47		S	
Dynamic C	haracterist	ics								
C _{iss}	Input Capa	citance	$V_{DS} = 25V, V_{GS} = 0V,$		\	3050	3970	pF		
C _{oss}	Output Ca	pacitance	f = 1.0 M	f = 1.0 MHz 			750	980	pF	
C _{rss}	Reverse Tr	ransfer Capacitance					89	130	pF	
Switching	Characteris	tics								
t _{d(on)}	Turn-On D	elay Time		00V, I _D = 70A			71	150	ns	
t _r	Turn-On R	ise Time	R _G = 25	R _G = 25Ω (Note 4)			235	480	ns	
t _{d(off)}	Turn-Off D	elay Time					65	140	ns	
t _f	Turn-Off Fa	all Time					39	88	ns	
Qg	Total Gate	Charge		$V_{DS} = 160V, I_D = 70A$ $V_{GS} = 10V$ (Note 4)			66	86	nC	
Q _{gs}	Gate-Sour	ce Charge	V _{GS} = 1				19		nC	
Q _{gd}	Gate-Drain	Charge				-	26		nC	
Drain-Sour	ce Diode C	haracteristics and Maxir	num Ratings	;						
I _S	Maximum Continuous Drain-Source Diode Forward Current					70	Α			
I _{SM}	Maximum	Pulsed Drain-Source Diod	ode Forward Current					280	Α	
V _{SD}	Drain-Sour	ce Diode Forward Voltage	e V _{GS} = 0	V _{GS} = 0V, I _S = 70A				1.4	V	
t _{rr}	Reverse R	ecovery Time		IV, I _S = 70A			175		ns	
Q _{rr}	Reverse R	ecovery Charge	dl _F /dt =	dI _F /dt =100A/μs			4.1		μC	

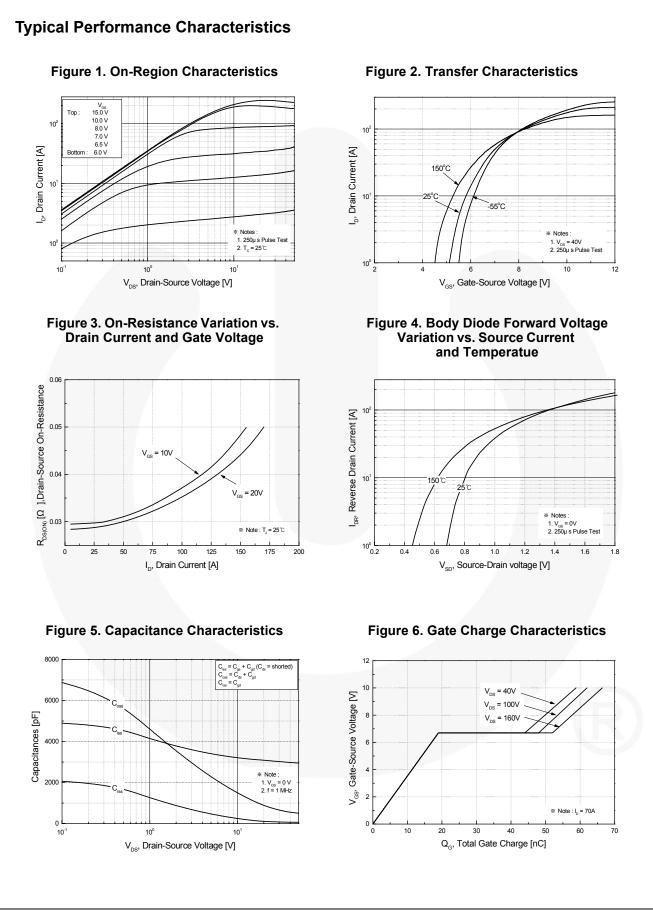
NOTES:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 0.533 mH, I_{AS} = 70 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting T_J = 25°C.

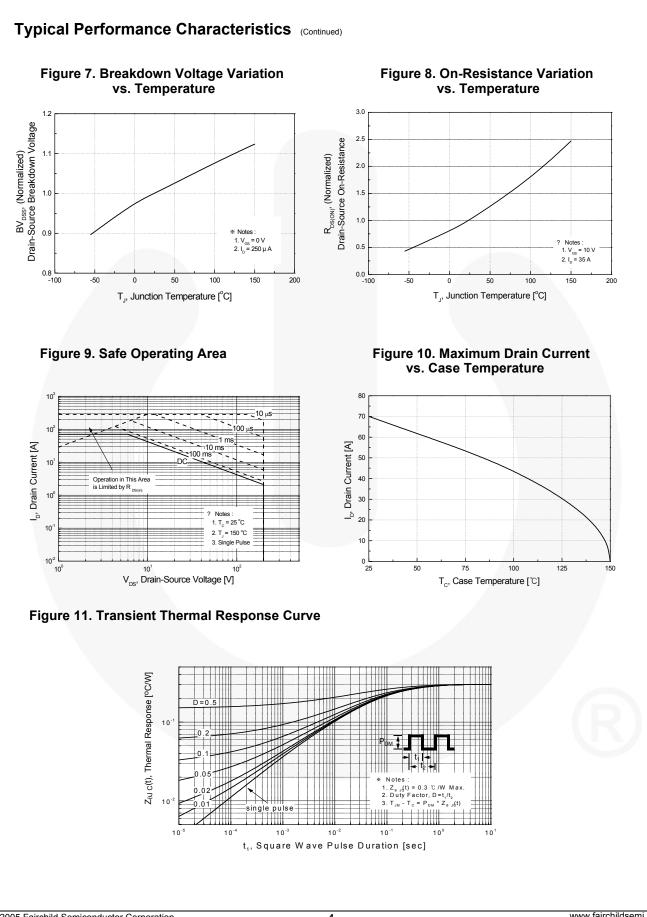
 $3.I_{SD} \leq$ 70 A, di/dt \leq 200 A/µs, $V_{DD} \leq BV_{DSS},$ starting T_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.



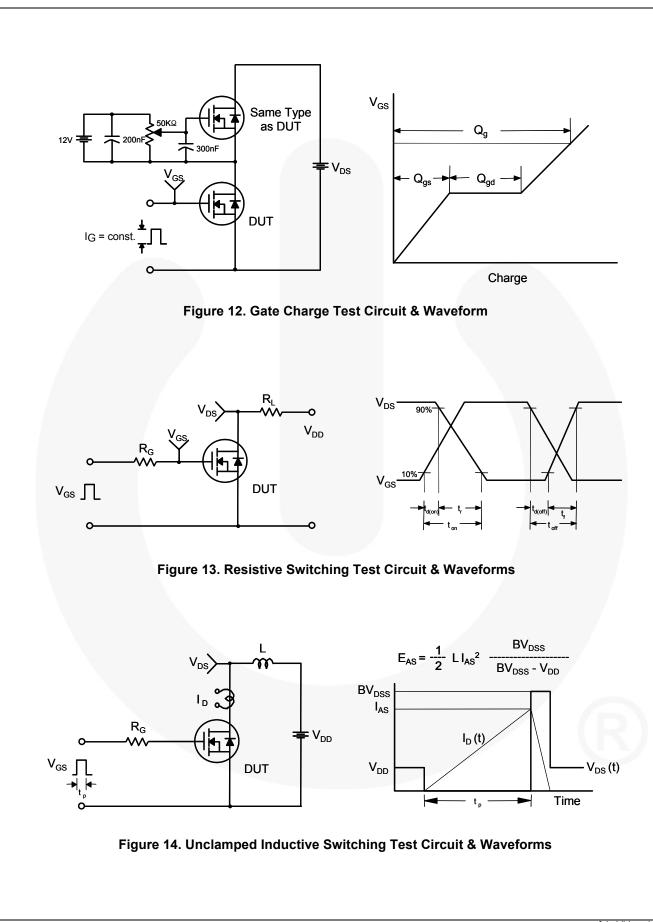
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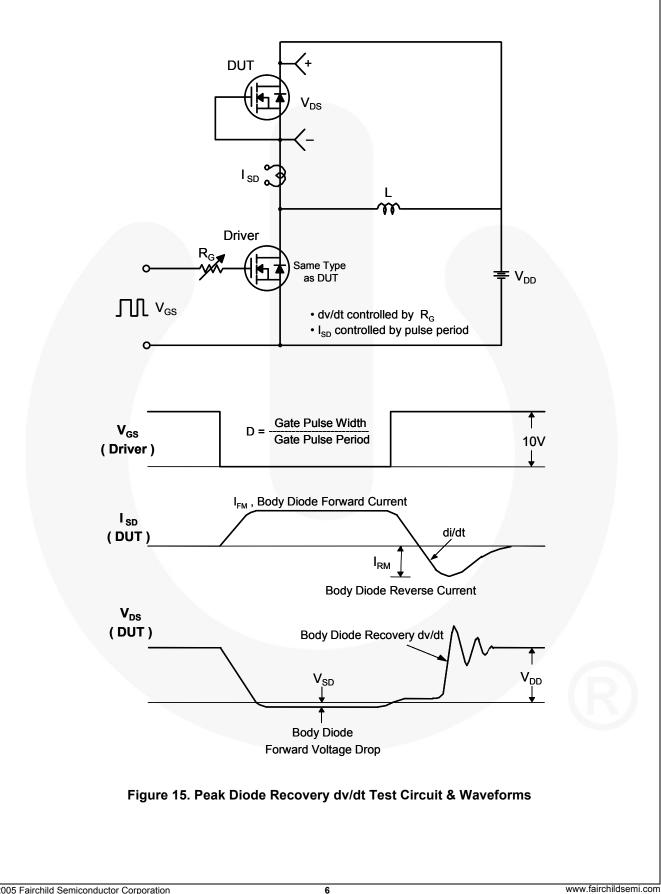


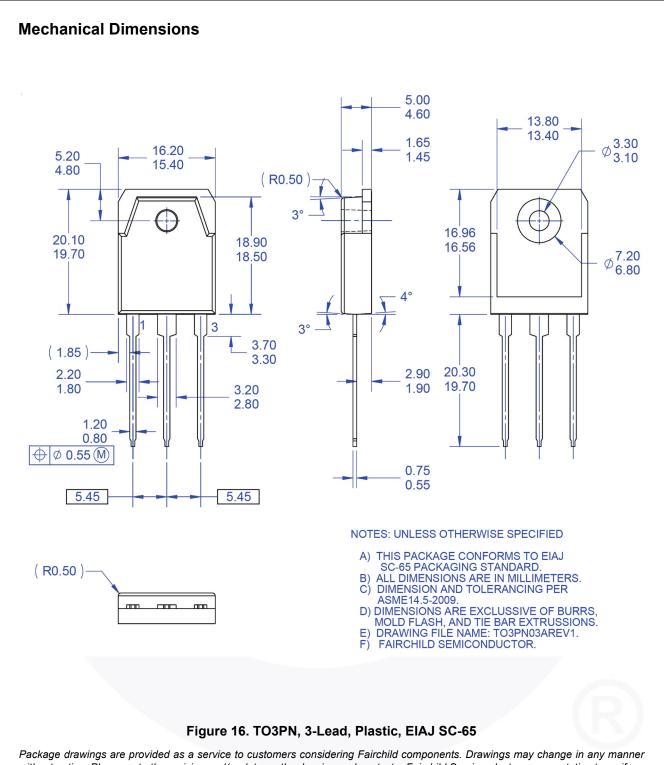
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